

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A semi-fusible link system for a multi-layer integrated circuit including active circuitry on a first layer having a metal one layer comprising:

a semi-fusible link element on a second layer having a metal two layer adapted for interconnecting with said metal one layer; and

a selector circuit disposed on said first layer.

2. (Original) The semi-fusible link system of claim 1 further including at least one interconnection coupling said metal one layer with said metal two layer for providing an electrical coupling between said semi-fusible link element and said active circuitry.

3. (Original) The semi-fusible link system of claim 1 further including an array of semi-fusible link elements disposed on said second layer.

4. (Original) The semi-fusible link system of claim 1 in which said selector circuit selects one of said array of said semi-fusible link elements.

5. (Original) The semi-fusible link system of claim 3 in which said selector circuit includes a transistor.

6. (Original) The semi-fusible link system of claim 5 in which said selector circuit includes an NMOS transistor.

7. (Original) The semi-fusible link system of claim 1 in which said selector circuit includes an NMOS transistor.

8. (Original) The semi-fusible link system of claim 1 in which said semi-fusible link element includes silicon chromium.

9. (Original) The semi-fusible link system of claim 1 in which said second layer is located above said first layer.

10. (Original) The semi-fusible link system of claim 1 in which said semi-fusible link is disposed above said active circuitry.

11. (Original) The semi-fusible link system of claim 1 in which said semi-fusible link is disposed above said active circuitry and said selector circuit.

12. (Original) The semi-fusible link system of claim 1 in which said active circuitry blows said semi-fusible link element to effect a change in a parameter of said integrated circuit.

13. (Original) The semi-fusible link system of claim 1 in which said selector circuit blows said semi-fusible link element to effect a change in a parameter of said integrated circuit selector circuit.

14. (Original) The semi-fusible link system of claim 1 in which said semi-fusible link element includes a thin film resistor.

15. (Original) A semi-fusible link system for a multi-layer integrated circuit including active circuitry on a first layer having a metal one layer, comprising:

a semi-fusible link element on a second layer having a metal two layer adapted for interconnecting with said metal one layer, said second layer being above said first layer;

at least one interconnection coupling said metal one layer with said metal two layer for providing an electrical coupling between said semi-fusible link element and said active circuitry; and

a selector circuit disposed on said first layer.

16. (Original) The semi-fusible link system of claim 15 in which said selector circuit includes a transistor.

17. (Original) The semi-fusible link system of claim 16 in which said selector circuit includes an NMOS transistor.

18. (Original) The semi-fusible link system of claim 15 in which said semi-fusible link element includes silicon chromium.

19. (Original) The semi-fusible link system of claim 15 in which said semi-fusible link element includes a thin film resistor.

20. (Original) The semi-fusible link system of claim 15 in which said semi-fusible link is disposed above said active circuitry.

21. (Original) The semi-fusible link system of claim 15 in which said semi-fusible link is disposed above said active circuitry and said selector circuit.

22. (Original) The semi-fusible link system of claim 15 in which said active circuitry blows said semi-fusible link element to effect a change in a parameter of said integrated circuit.

23. (Original) The semi-fusible link system of claim 15 in which said selector circuit blows said semi-fusible link element to effect a change in a parameter of said integrated circuit selector circuit.

24. (Original) A semi-fusible link system for a multi-layer integrated circuit including active circuitry on a first layer having a metal one layer, comprising:

a thin film resistor semi-fusible link element on a second layer having a metal two layer adapted for interconnecting with said metal one layer, said second layer being above said first layer;

at least one interconnection coupling said metal one layer to said metal two layer for providing an electrical coupling between said semi-fusible link element and said active circuitry; and

a selector circuit including a select transistor disposed on said first layer.

25. (Original) The semi-fusible link device of claim 24 in which said semi-fusible link element includes silicon chromium.

26. (Original) The semi-fusible link system of claim 24 in which said semi-fusible link is disposed above said active circuitry.

27. (Original) The semi-fusible link system of claim 24 in which said semi-fusible link is disposed above said active circuitry and said selector circuit.

28. (Original) The semi-fusible link system of claim 24 in which said active circuitry blows said semi-fusible link element to effect a change in a parameter of said integrated circuit.

29. (Original) The semi-fusible link system of claim 24 in which said selector circuit blows said semi-fusible link element to effect a change in a parameter of said integrated circuit selector circuit.

30. (Original) A semi-fusible link system for a multi-layer integrated circuit including active circuitry on a first layer having a metal one layer comprising:

a semi-fusible link element on a second layer having a metal two layer adapted for interconnecting with said metal one layer; and

a selector circuit disposed on said first layer, one of said active circuitry and said selector circuit for blowing said semi-fusible link element to effect a change in a parameter in said integrated circuit.

31-34. (Cancelled)